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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

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Keep safety first in your circuit designs!

1. Renesas Technology Corporation puts the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury, fire or property damage.

Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

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2SC2855, 2SC2856

Silicon NPN Epitaxial

RENESAS

ADE-208-1079 (Z)
1st. Edition
Mar. 2001

Application

- Low frequency low noise amplifier
- Complementary pair with 2SA1190 and 2SA1191

Outline

TO-92 (1)



1. Emitter
2. Collector
3. Base

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	2SC2855	2SC2856	Unit
Collector to base voltage	V _{CBO}	90	120	V
Collector to emitter voltage	V _{CEO}	90	120	V
Emitter to base voltage	V _{EB0}	5	5	V
Collector current	I _C	100	100	mA
Emitter current	I _E	−100	−100	mA
Collector power dissipation	P _C	400	400	mW
Junction temperature	T _j	150	150	°C
Storage temperature	T _{stg}	−55 to +150	−55 to +150	°C

Not recommended
for new design

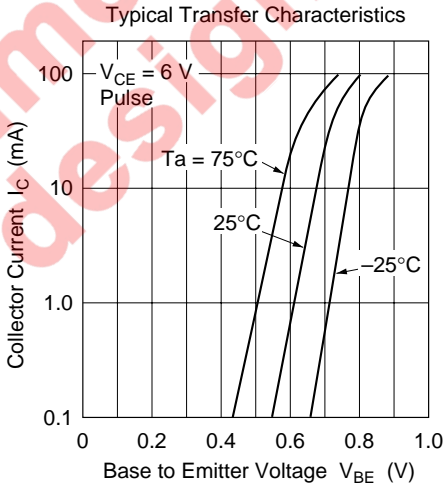
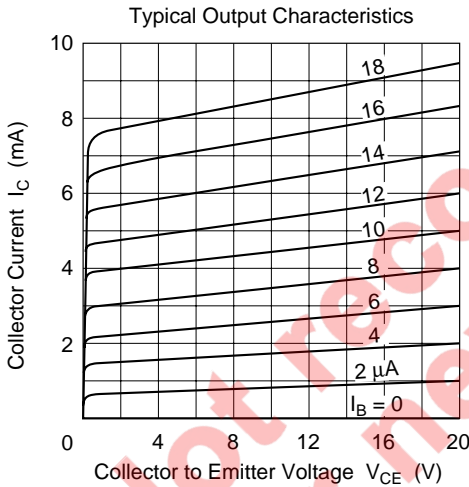
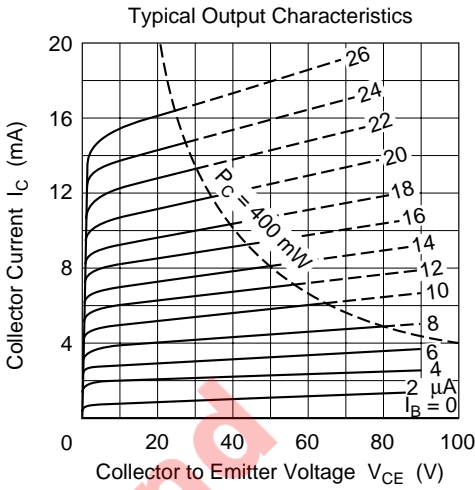
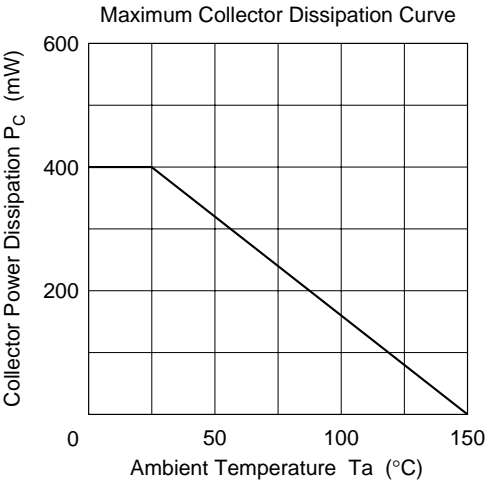
Electrical Characteristics (Ta = 25°C)

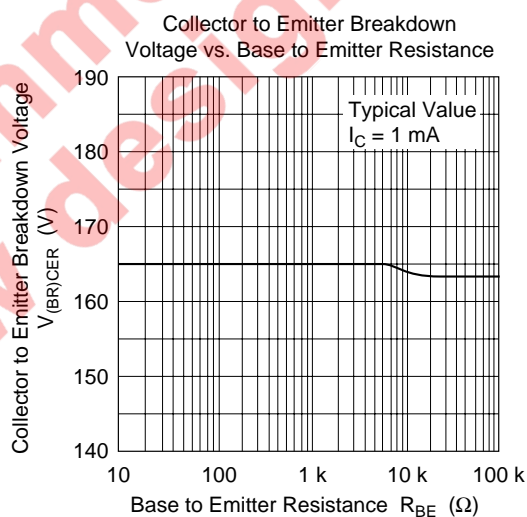
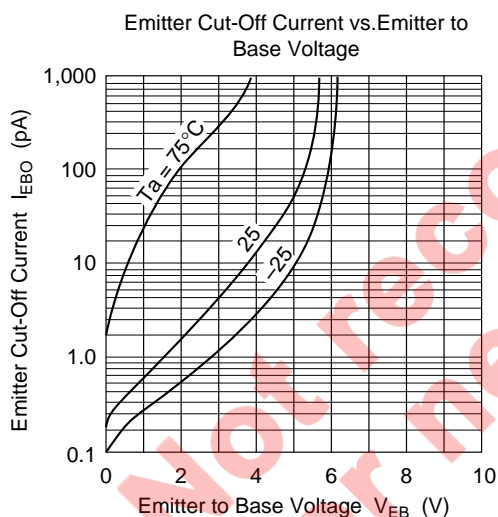
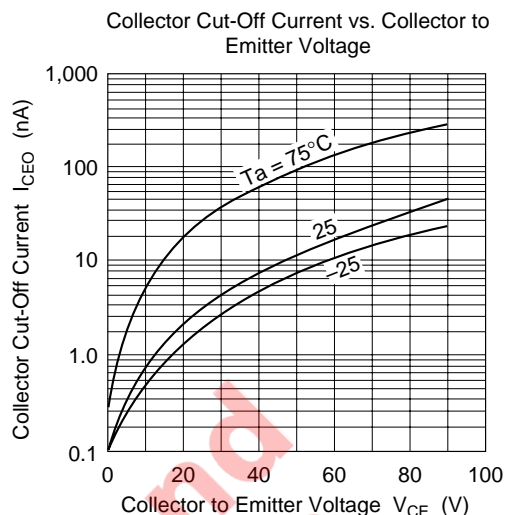
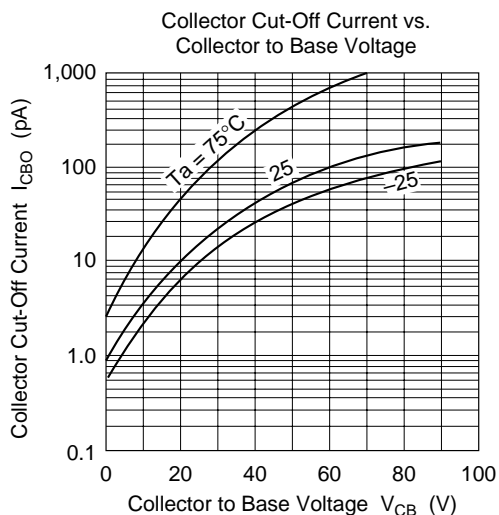
Item	Symbol	2SC2855			2SC2856			Unit	Test conditions
		Min	Typ	Max	Min	Typ	Max		
Collector to base breakdown voltage	$V_{(BR)CBO}$	90	—	—	120	—	—	V	$I_C = 10\text{ }\mu\text{A}$, $I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	90	—	—	120	—	—	V	$I_C = 1\text{ mA}$, $R_{BE} =$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	5	—	—	5	—	—	V	$I_E = 10\text{ }\mu\text{A}$, $I_C = 0$
Collector cutoff current	I_{CBO}	—	—	0.1	—	—	0.1	μA	$V_{CB} = 70\text{ V}$, $I_E = 0$
Emitter cutoff current	I_{EBO}	—	—	0.1	—	—	0.1	μA	$V_{EB} = 2\text{ V}$, $I_C = 0$
DC current transfer ratio	h_{FE}^{*1}	250	—	800	250	—	800		$V_{CE} = 12\text{ V}$, $I_C = 2\text{ mA}^{*2}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	0.05	0.10	—	0.05	0.10	V	$I_C = 10\text{ mA}$, $I_B = 1\text{ mA}^{*2}$
Base to emitter saturation voltage	$V_{BE(sat)}$	—	0.7	1.0	—	0.7	1.0	V	
Gain bandwidth product	f_T	—	310	—	—	310	—	MHz	$V_{CE} = 6\text{ V}$, $I_C = 10\text{ mA}$
Collector output capacitance	C_{ob}	—	3	—	—	3	—	pF	$V_{CB} = 10\text{ V}$, $I_E = 0$, $f = 1\text{ MHz}$
Noise figure	NF	—	0.15	1.5	—	0.15	1.5	dB	$V_{CE} = 6\text{ V}$, $I_C = 0.1\text{ mA}$, $R_g = 10\text{ k}\Omega$, $f = 1\text{ kHz}$
		—	0.2	2.0	—	0.2	2.0	dB	$V_{CE} = 6\text{ V}$, $I_C = 0.1\text{ mA}$, $R_g = 10\text{ k}\Omega$, $f = 10\text{ Hz}$
Noise voltage referred to input	e_n	—	0.7	—	—	0.7	—	$\text{nV}/\sqrt{\text{Hz}}$	$V_{CE} = 6\text{ V}$, $I_C = 10\text{ mA}$, $R_g = 0$, $f = 1\text{ kHz}$

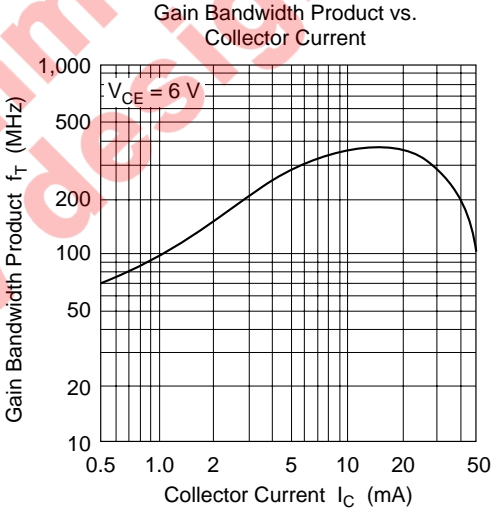
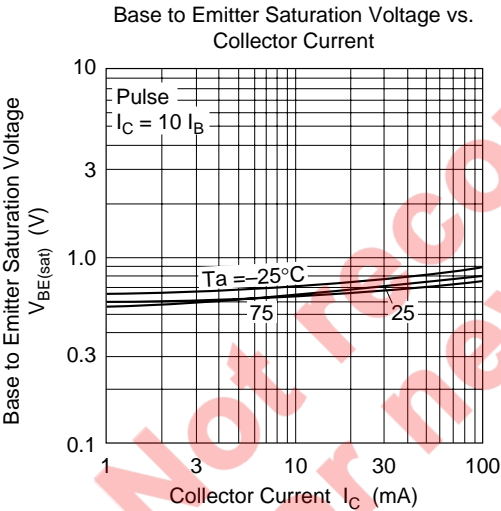
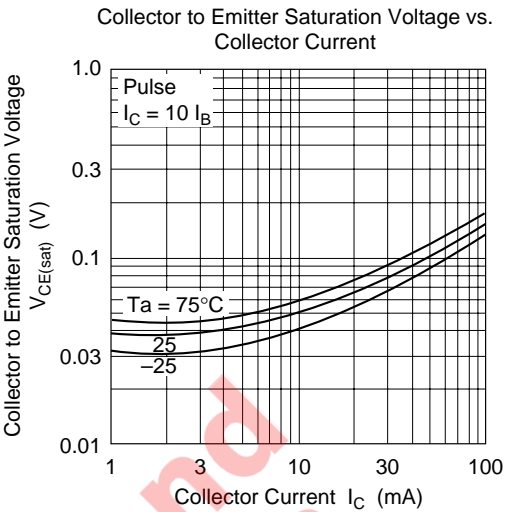
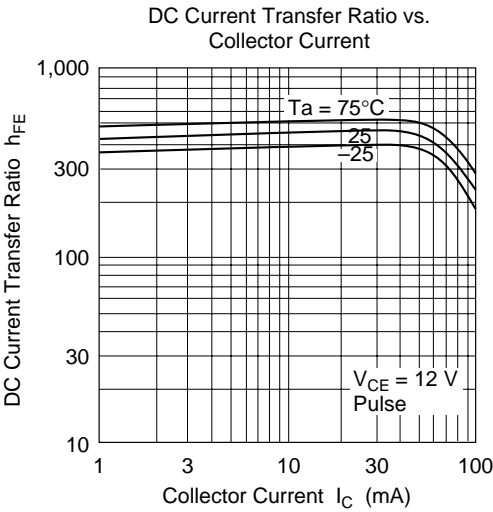
Notes: 1. The 2SC2855 and 2SC2856 are grouped by h_{FE} as follows.

2. Pulse test

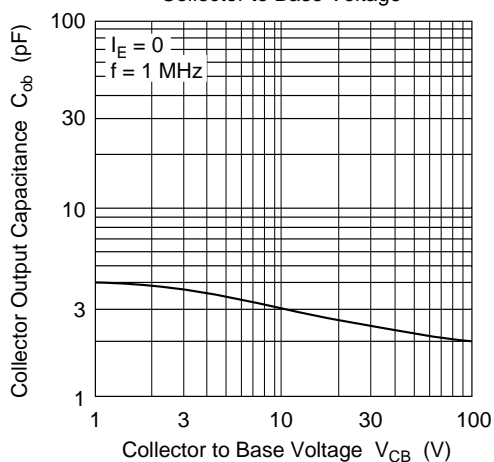
D	E
250 to 500	400 to 800



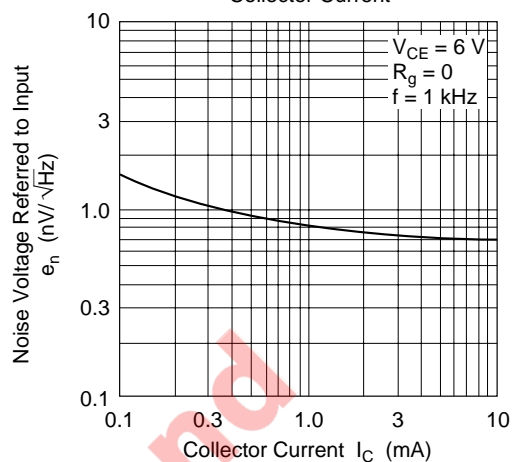




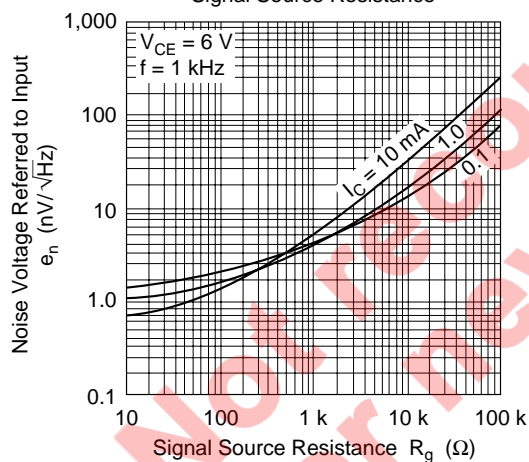
Collector Output Capacitance vs.
Collector to Base Voltage



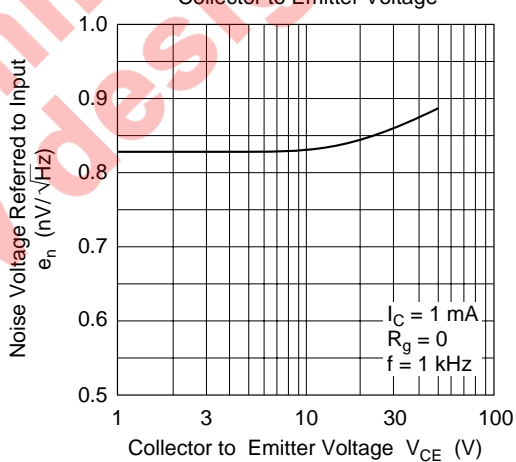
Noise Voltage Referred to Input vs.
Collector Current



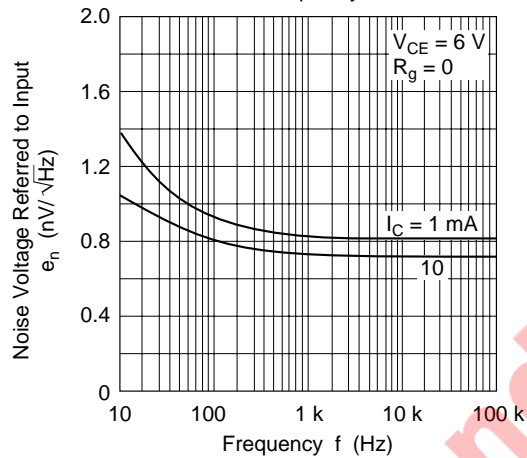
Noise Voltage Referred to Input vs.
Signal Source Resistance



Noise Voltage Referred to Input vs.
Collector to Emitter Voltage



Noise Voltage Referred to Input vs.
Frequency

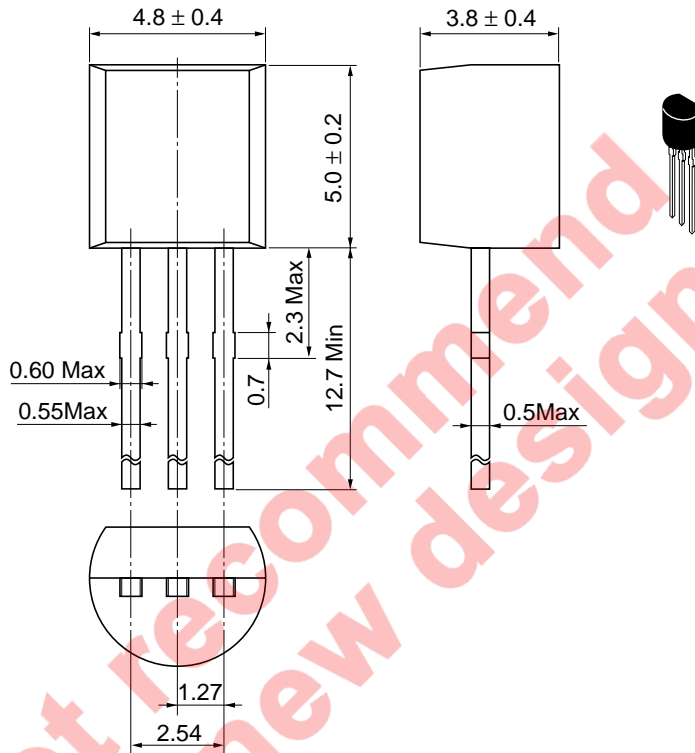


Not recommended
for new design

Package Dimensions

As of January, 2001

Unit: mm



Hitachi Code	TO-92 (1)
JEDEC	Conforms
EIAJ	Conforms
Mass (reference value)	0.25 g

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HITACHI

Hitachi, Ltd.

Semiconductor & Integrated Circuits.

Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan

Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

URL	NorthAmerica	: http://semiconductor.hitachi.com/
	Europe	: http://www.hitachi-eu.com/hel/ecg
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For further information write to:

Hitachi Semiconductor
(America) Inc.
179 East Tasman Drive,
San Jose, CA 95134
Tel: <1> (408) 433-1990
Fax: <1> (408) 433-0223

Hitachi Europe GmbH
Electronic Components Group
Dornacher Straße 3
D-85622 Feldkirchen, Munich
Germany
Tel: <49> (89) 9 9180-0
Fax: <49> (89) 9 29 30 00

Hitachi Europe Ltd.
Electronic Components Group.
Whitebrook Park
Lower Cookham Road
Maidenhead
Berkshire SL6 8YA, United Kingdom
Tel: <44> (1628) 585000
Fax: <44> (1628) 585160

Hitachi Asia Ltd.
Hitachi Tower
16 Collyer Quay #20-00,
Singapore 049318
Tel: <65>-538-6533/538-8577
Fax: <65>-538-6933/538-3877
URL: <http://www.hitachi.com.sg>

Hitachi Asia Ltd.
(Taipei Branch Office)
4/F, No. 167, Tun Hwa North Road,
Hung-Kuo Building,
Taipei (105), Taiwan
Tel: <886>-(2)-2718-3666
Fax: <886>-(2)-2718-8180
Telex: 23222 HAS-TP
URL: <http://www.hitachi.com.tw>

Hitachi Asia (Hong Kong) Ltd.
Group III (Electronic Components)
7/F., North Tower,
World Finance Centre,
Harbour City, Canton Road
Tsim Sha Tsui, Kowloon,
Hong Kong
Tel: <852>-(2)-735-9218
Fax: <852>-(2)-730-0281
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